

# CNA1007H

## Photo Interrupter

For contactless SW, object detection

### Overview

CNA1007H is a transmissive photosensor in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

### Features

- Position detection accuracy : 0.3 mm
- Gap width : 5 mm
- Horizontal slit type
- The type directly attached to PCB ( with a positioning pins)

### Absolute Maximum Ratings (Ta = 25°C)

Parameter		Symbol	Ratings	Unit
Input (Light emitting diode)	Reverse voltage (DC)	$V_R$	5	V
	Forward current (DC)	$I_F$	50	mA
	Power dissipation	$P_D^{*1}$	75	mW
Output (Photo transistor)	Collector current	$I_C$	20	mA
	Collector to emitter voltage	$V_{CEO}$	30	V
	Emitter to collector voltage	$V_{ECO}$	5	V
Temperature	Collector power dissipation	$P_C^{*2}$	100	mW
	Operating ambient temperature	$T_{opr}$	-25 to +85	°C
	Storage temperature	$T_{stg}$	-40 to +100	°C

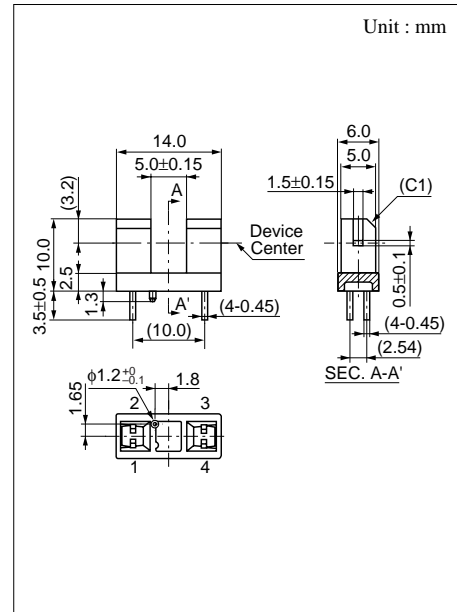
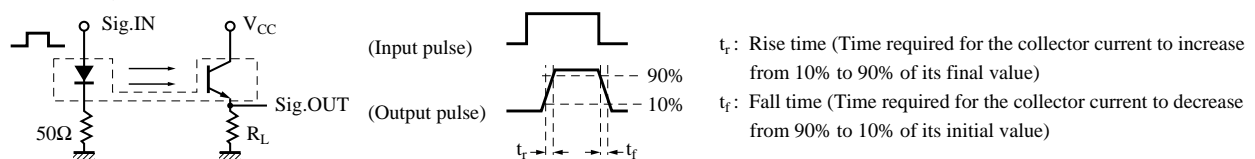
\*1 Input power derating ratio is 1.0 mW/°C at Ta = 25°C.

\*2 Output power derating ratio is 1.33 mW/°C at Ta = 25°C.

### Electrical Characteristics (Ta = 25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Input characteristics	Forward voltage (DC)	$V_F$	$I_F = 20\text{mA}$		1.25	1.4	V
	Reverse current (DC)	$I_R$	$V_R = 3\text{V}$			10	$\mu\text{A}$
Output characteristics	Collector cutoff current	$I_{CEO}$	$V_{CE} = 10\text{V}$			200	nA
Transfer characteristics	Collector current	$I_C$	$V_{CE} = 5\text{V}, I_F = 20\text{mA}$	0.5		14	mA
	Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_F = 40\text{mA}, I_C = 1\text{mA}$			0.4	V
	Response time	$t_r, t_f^*$	$V_{CC} = 5\text{V}, I_C = 1\text{mA}, R_L = 100\Omega$		5		$\mu\text{s}$

\* Switching time measurement circuit



Internal connector

